

JST41Z-600B 40A TRIAC

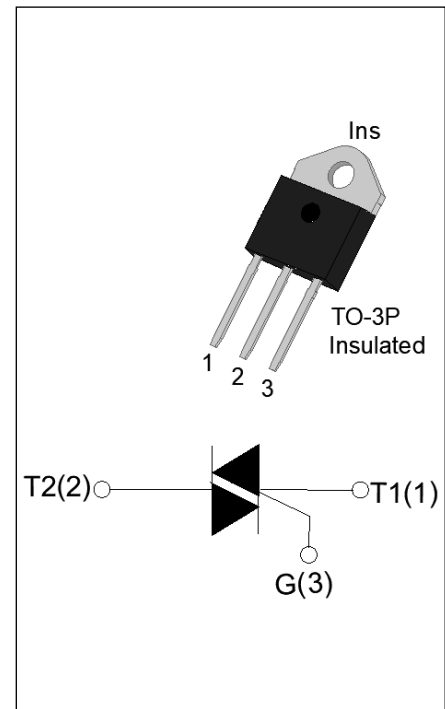
Rev.A.1.1

DESCRIPTION:

The JST41Z-600B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. By using an internal ceramic pad, JST41Z-600B provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-3P is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III/IV}$	50/50/50/70	mA


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	℃
Operating junction temperature range		T _j	-40-125	℃
Repetitive peak off-state voltage (T _j =25℃)		V _{DRM}	600	V
Repetitive peak reverse voltage (T _j =25℃)		V _{RRM}	600	V
RMS on-state current (T _c ≤81℃)		I _{T(RMS)}	40	A
Non repetitive surge peak on-state current (full cycle , t _p =20ms , T _j =25℃)		I _{TSM}	420	A
Non repetitive surge peak on-state current (full cycle , t _p =16.6ms , T _j =25℃)			462	
I ² t value for fusing (t _p =10ms , T _j =25℃)		I ² t	1000	A ² s
Critical rate of rise of on-state current (I _G =2×I _{GT} , f=100Hz , T _j =125℃)	I - II	di/dt	100	A/μs
	III-IV		50	
Peak gate current (t _p =20μs , T _j =125℃)		I _{GM}	8	A
Average gate power dissipation (T _j =125℃)		P _{G(AV)}	1	W
Peak gate power		P _{GM}	40	W

Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	0.9	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
		IV		70	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX.	80	mA
		II		160	
I_H	$I_T=500\text{mA}$		MAX.	80	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN.	1500	V/ μs
$(dV/dt)_c$	$(dI/dt)_c=20\text{A/ms}$, $T_j=125^{\circ}\text{C}$		MIN.	20	V/ μs
t_{on}	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	10	μs
t_{off}				70	

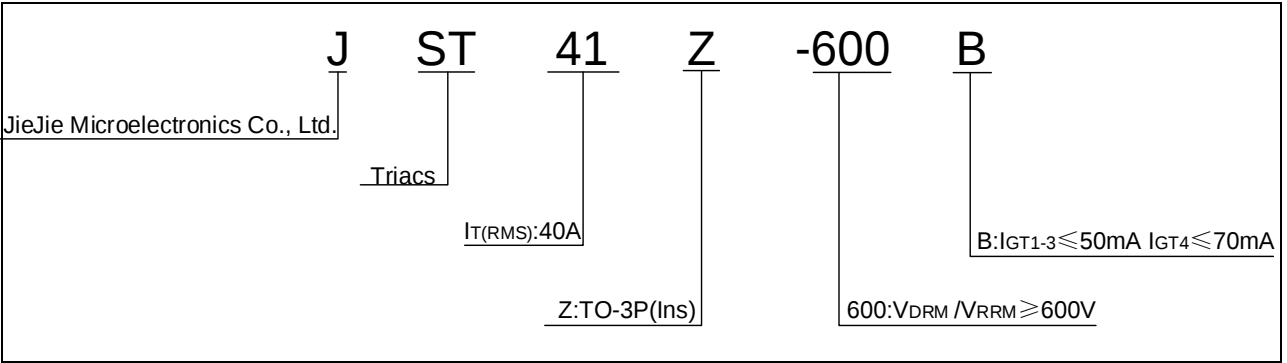
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=60\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.73	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	10	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.85	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	50	$^{\circ}\text{C/W}$

ORDERING INFORMATION



MARKING

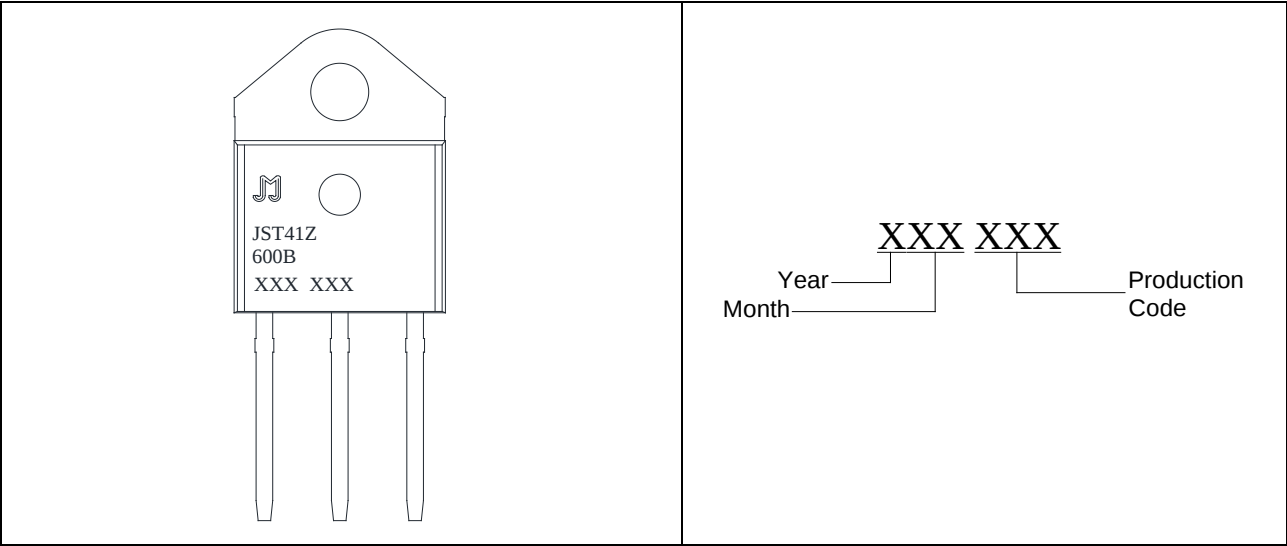


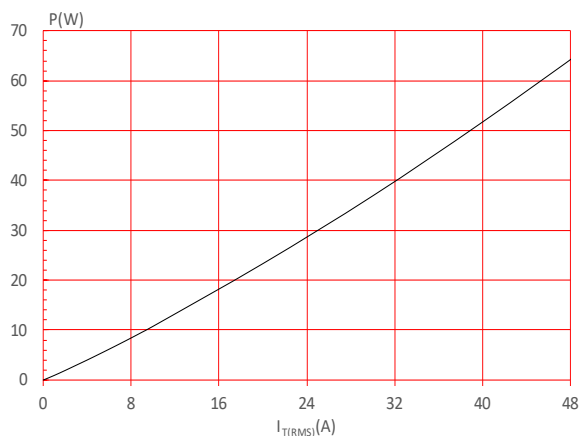
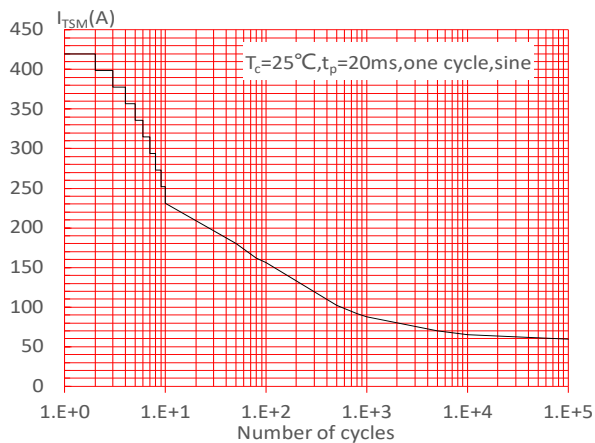
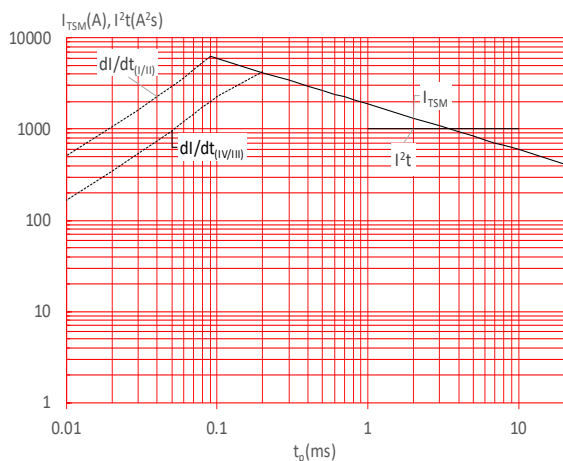
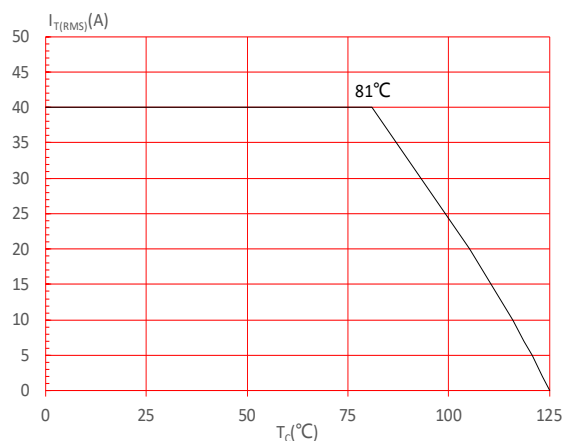
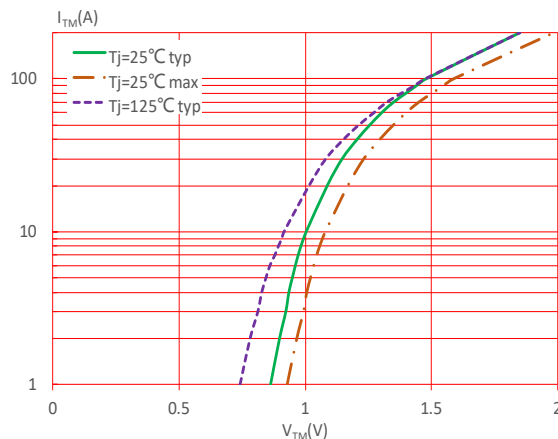
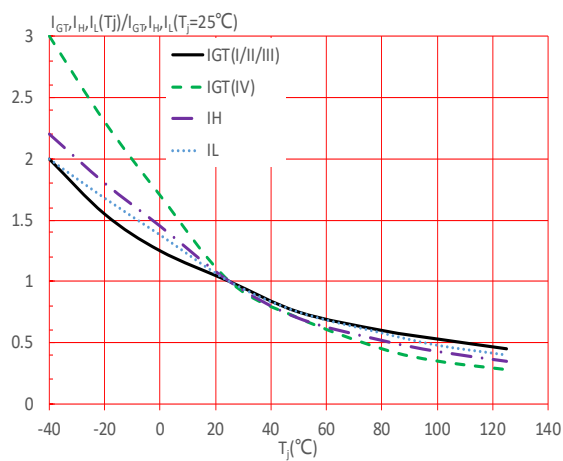
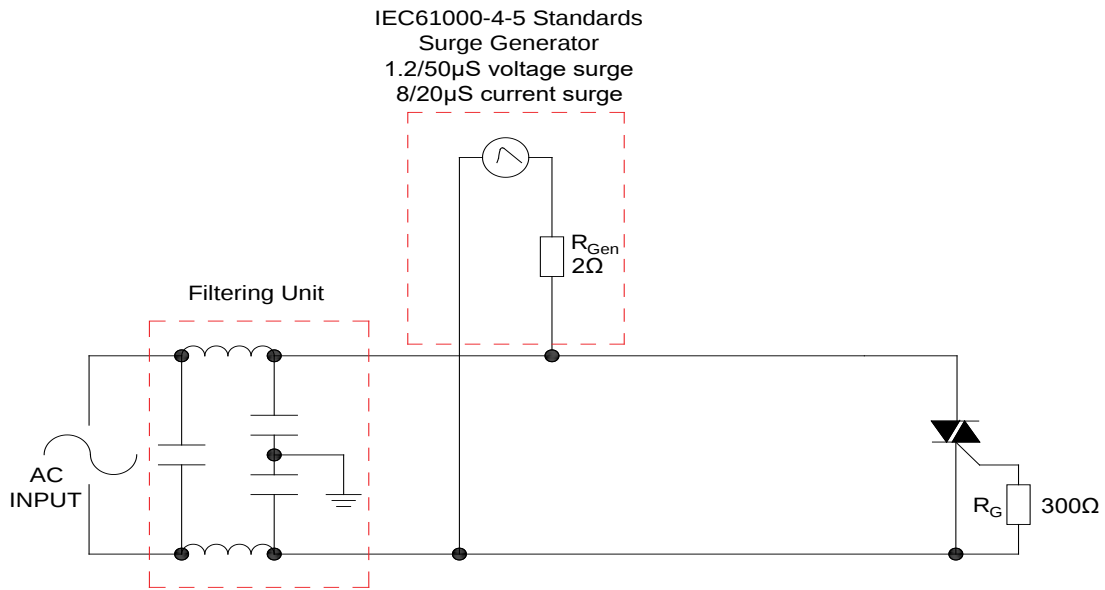
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II: $di/dt < 100\text{A}/\mu\text{s}$; III-IV: $di/dt < 50\text{A}/\mu\text{s}$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

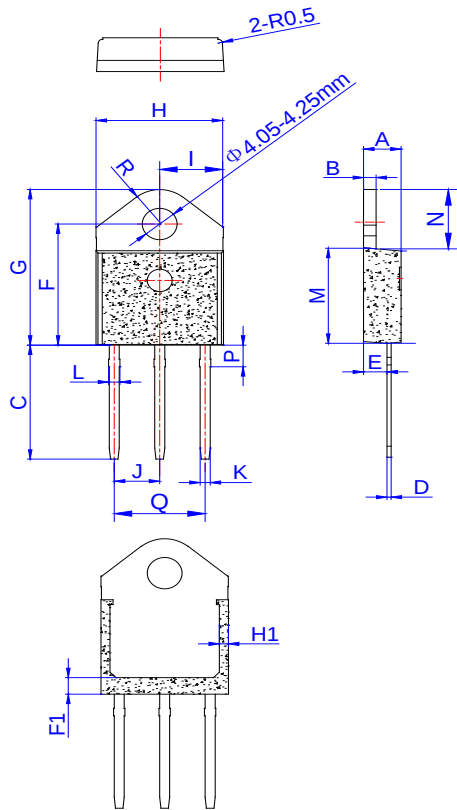
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
JST41Z-600B	600	50	70	TO-3P(Ins)	30	Tube

Document Revision History

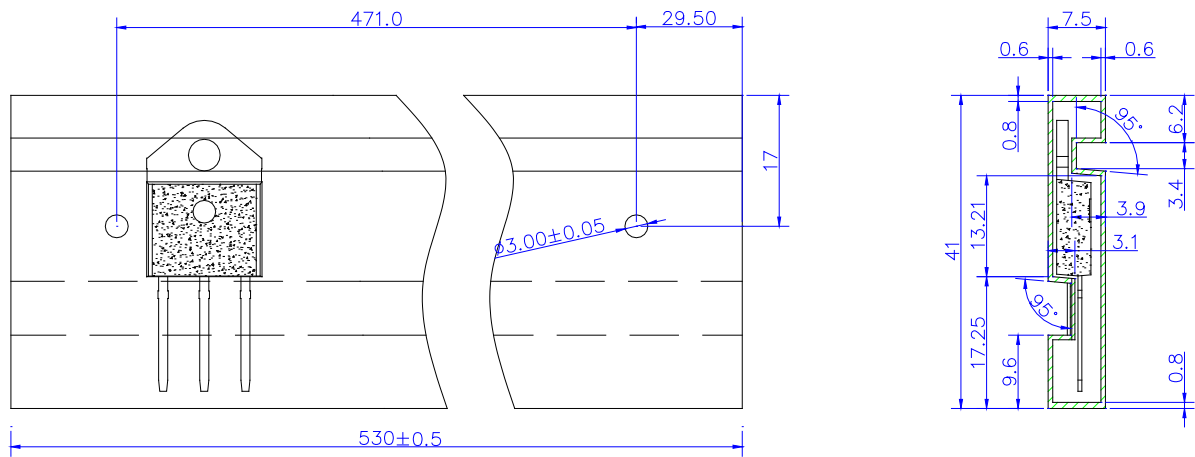
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated
Oct.17, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
F1	2.45		2.85	0.096		0.112
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
H1	1.10		1.50	0.043		0.059
I	7.25		7.65	0.285		0.301
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.25		1.45	0.049		0.057
M	12.37		12.77	0.487		0.503
N	7.80		8.20	0.307		0.323
P	2.80		3.00	0.110		0.118
Q	10.70		11.10	0.421		0.437
R		4.35			0.171	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-3P	TUBE	30	450	2,250

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